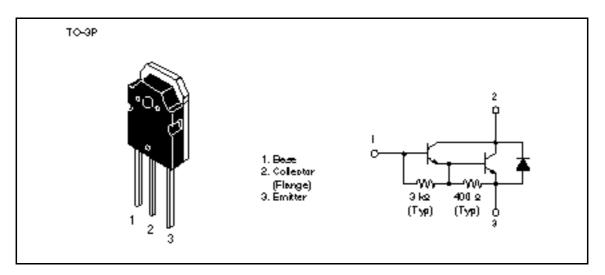
Silicon NPN Triple Diffused

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### Application

Low frequency power amplifier complementary pair with 2SB1079

### Outline



# **Absolute Maximum Ratings** (Ta = $25^{\circ}$ C)

Item	Symbol	Ratings	Unit V	
Collector to base voltage	V <sub>CBO</sub>	100		
Collector to emitter voltage	V <sub>CEO</sub>	100	V	
Emitter to base voltage	$V_{EBO}$	7	V	
Collector current	Ι <sub>c</sub>	20	A A A W	
Collector peak current	I <sub>C(peak)</sub>	30		
Base current	Ι <sub>Β</sub>	3		
Collector power dissipation	P <sub>c</sub> *1	100		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	
Noto: 1 Value at $T = 25^{\circ}C$				

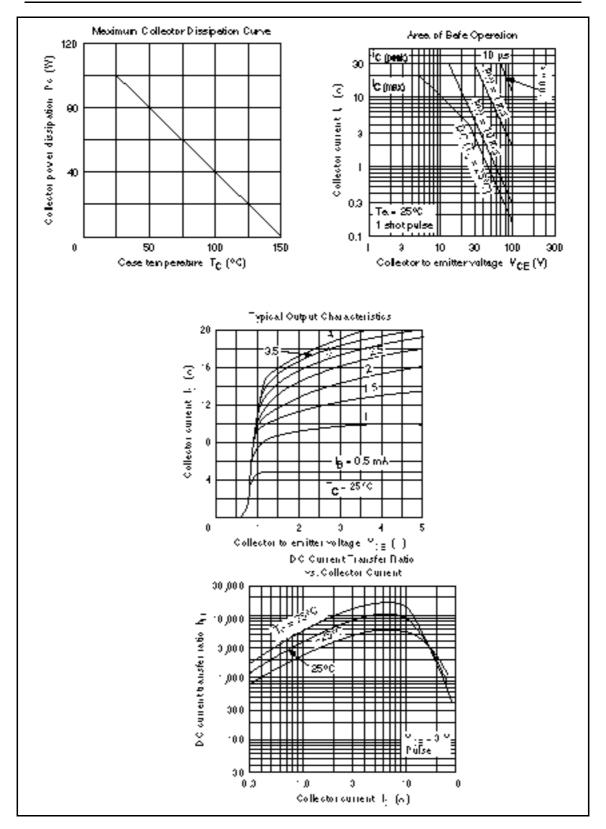
Note: 1. Value at  $T_c = 25^{\circ}C$ .



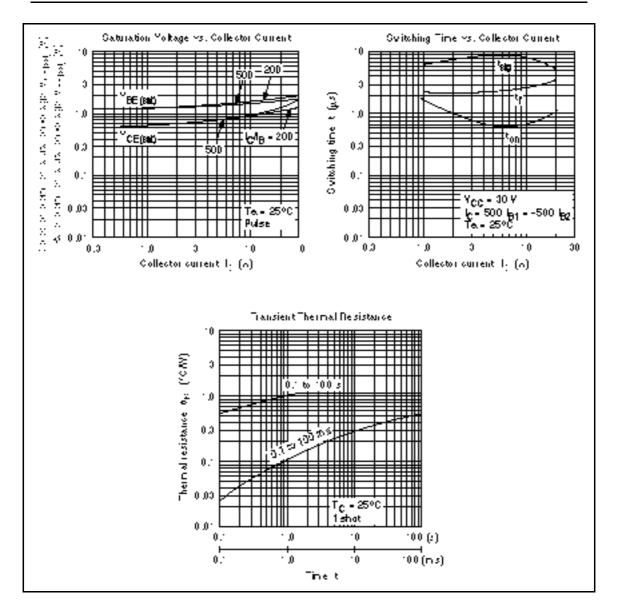
# **Electrical Characteristics** (Ta = $25^{\circ}$ C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	100	—		V	$I_{c} = 0.1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	100	—	_	V	$I_{c} = 25 \text{ mA}, R_{BE} =$
Collector to emitter sustain voltage	$V_{\text{CEO}(\text{sus})}$	100	—	_	V	$I_{c} = 200 \text{ mA}, R_{BE} = *^{1}$
Emitter to base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	7	—	_	V	$V_{EB} = 50 \text{ mA}, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	100	μA	$V_{CB} = 100 \text{ V}, I_{E} = 0$
	I <sub>CEO</sub>	_	_	1.0	mA	$V_{ce} = 80 \text{ V}, \text{ R}_{be} =$
DC current transfer ratio	h <sub>FE</sub>	1000	—	20000		$V_{ce} = 3 \text{ V}, I_c = 10 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})1}$	_	_	2.0	V	$I_{c} = 10 \text{ A}, I_{B} = 20 \text{ mA}^{*1}$
Base to emitter saturatiopn voltage	$V_{\text{BE(sat)1}}$	_	_	2.5	V	_
Collector to emitter saturation voltage	$V_{\text{CE(sat)2}}$	_	_	3.0	V	$I_{c} = 20 \text{ A}, I_{B} = 200 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)^2}$	—	—	3.5	V	_
Turn on time	t <sub>on</sub>	_	1.0		μs	$I_{\rm C} = 10 \text{ A}, I_{\rm B1} = -I_{\rm B2} = 20 \text{ mA}$
Storage time	t <sub>stg</sub>	_	9.0		μs	_
Fall time	t <sub>r</sub>		3.0		μs	_

Note: 1. Pulse test.



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